# Constant Voltage / Constant Current Secondary-Side Controller

#### Description

The NCS1002A is a performance upgrade from the NCS1002 focused on reducing power consumption in applications that require more efficient operation. It is a highly integrated solution for Switching Mode Power Supply (SMPS) applications requiring a dual control loop to perform Constant Voltage (CV) and Constant Current (CC) regulation. The NCS1002A integrates a 2.5 V voltage reference and two precision op amps. The voltage reference, along with Op Amp 1, is the core of the voltage control-loop. Op Amp 2 is an independent, uncommitted amplifier specifically designed for the current control. Key external components needed to complete the two control loops are: (a) A resistor divider that senses the output of the power supply (battery charger) and fixes the voltage regulation set point at the specified value. (b) A sense resistor that feeds the current sensing circuit with a voltage proportional to the DC output current. This resistor determines the current regulation set point and must be adequately rated in terms of power dissipation. The NCS1002A comes in a small 8-pin SOIC package and is ideal for space-shrunk applications such as battery chargers.

#### **Features**

- Low Input Offset Voltage: 0.5 mV, Typ
- Input Common-Mode Range includes Ground
- Low Quiescent Current: 75  $\mu$ A per Op Amp at  $V_{CC} = 5 \text{ V}$
- Large Output Voltage Swing
- Wide Power Supply Range: 3 V to 36 V
- High ESD Protection: 2 kV
- This is a Pb-Free Device

#### **Typical Applications**

- Battery Chargers
- Switch Mode Power Supplies



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#### MARKING DIAGRAMS



SOIC-8 D SUFFIX CASE 751



= Assembly Location

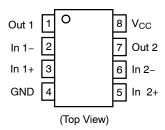
L = Wafer Lot Y = Year

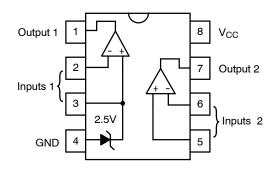
W = Work Week

= Pb-Free Package

(Note: Microdot may be in either location)

#### **PIN CONNECTIONS**





#### ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 8 of this data sheet.

#### **MAXIMUM RATINGS**

Parameter	Symbol	Rating	Unit
Supply Voltage (V <sub>CC</sub> to GND) (Operating Range V <sub>CC</sub> = 3 V to 36 V)	V <sub>CC</sub>	36	V
Differential Input Voltage	V <sub>id</sub>	36	V
Input Voltage	V <sub>i</sub>	-0.3 to +36	V
ESD Protection Voltage at Pin Human Body Model	V <sub>ESD</sub>	2000	V
Maximum Junction Temperature	TJ	150	°C
Specification Temperature Range (T <sub>min</sub> to T <sub>max</sub> )	T <sub>A</sub>	-40 to +105	°C
Operating Free-Air Temperature Range	T <sub>oper</sub>	-55 to +125	°C
Storage Temperature Range	T <sub>stg</sub>	-65 to +150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

#### THERMAL CHARACTERISTICS

Ī	F	Parameter	Symbol	Rating	Unit
ſ	Thermal Resistance	Junction-to-Ambient	$R_{\theta JA}$	175	°C/W

#### **ELECTRICAL CHARACTERISTICS**

Symbol	Characteristics	Conditions	Min	Тур	Max	Unit
I <sub>CC</sub>	Total Supply Current, excluding current in the Voltage Reference $V_{CC}$ = 5 V, no load; $-40 \le T_A \le +105^{\circ}C$			0.15	0.25	mA
I <sub>CC</sub>	Total Supply Current, excluding Current in the Voltage Reference $V_{CC}$ = 30 V, no load; $-40 \le T_A \le +105^{\circ}C$			0.2	0.3	mA

# OP AMP 1 (OP AMP WITH NONINVERTING INPUT CONNECTED TO THE INTERNAL $V_{ref}$ (V $_{CC}$ = 5 V, T $_{A}$ = 25°C unless otherwise noted)

$V_{IO}$	Input Offset Voltage	T <sub>A</sub> = 25°C			2.0	mV
		$-40 \le T_A \le +105^{\circ}C$			3.0	mV
DV <sub>IO</sub>	Input Offset Voltage Drift ( $-40 \le T_A \le +105^{\circ}C$ )			7.0		μV/°C
I <sub>IB</sub>	Input Bias Current (Inverting Input Only)			20	150	nA
AVD	Large Signal Voltage Gain ( $V_{CC}$ = 15 V, $R_L$ = 2 k $\Omega$ , $V_{ICM}$ = 0 V)			100		V/mV
PSRR	Power Supply Rejection (V <sub>CC</sub> = 5.0 V to 30 V, V <sub>OUT</sub> = 2 V)		80	100		dB
Isource	Output Source Current ( $V_{CC}$ = 15 V, $V_{OUT}$ = 2.0 V, $V_{id}$ = 1 V)		20	40		mA
I <sub>O</sub>	Short Circuit to GND (V <sub>CC</sub> = 15 V)			40	60	mA
I <sub>SINK</sub>	Output Current Sink (V <sub>id</sub> = -1 V)	V <sub>CC</sub> = +15 V, V <sub>OUT</sub> = 0.2 V (Note 1)	1	10		mA
		V <sub>CC</sub> = +15 V, V <sub>OUT</sub> = 2 V	10	20		mA
V <sub>OH</sub>	Output Voltage Swing, High (V <sub>CC</sub> = 30 V)	$R_L = 2 \text{ k}\Omega$ , $T_A = 25^{\circ}\text{C}$	26	27		V
		$-40 \le T_A \le +105^{\circ}C$	26			
		$R_L = 10 \text{ k}\Omega$ , $T_A = 25^{\circ}\text{C}$	27	28		
		$-40 \le T_A \le +105^{\circ}C$	27			1
V <sub>OL</sub>	Output Voltage Swing, Low	$R_L = 10 \text{ k}\Omega$ , $T_A = 25^{\circ}\text{C}$		5.0	50	mV
SR	Slew Rate (AV = +1, $V_i$ = 0.5 V to 2 V, $V_{CC}$ = 15 V, $R_L$ = 2 k $\Omega$ , $C_L$ = 100 pF)		0.2	0.4		V/μs
GBP	Gain Bandwidth Product ( $V_{CC}$ = 30 V, AV = +1, (Not R <sub>L</sub> = 2 k $\Omega$ , C <sub>L</sub> = 100 pF, f = 100 kHz, V <sub>IN</sub> = 10 mV <sub>PF</sub>		0.5	0.9		MHz
THD	Total Harmonic Distortion (f = 1 kHz, AV = 10, $R_L = 2 k\Omega$ , $V_{CC} = 30 V$ , $V_{OUT} = 2 V_{PP}$ )			0.08		%

## **OP AMP 2 (INDEPENDENT OP AMP)** $(V_{CC} = 5.0 \text{ V}, T_A = 25^{\circ}\text{C unless otherwise noted})$

V <sub>IO</sub>	Input Offset Voltage	T <sub>A</sub> = 25°C		0.5	2.0	mV
		$-40 \le T_A \le +105^{\circ}C$			3.0	
DV <sub>IO</sub>	Input Offset Voltage Drift ( $-40 \le T_A \le +105^{\circ}C$ )			7.0		μV/°C
I <sub>IO</sub>	Input Offset Current	T <sub>A</sub> = 25°C		2.0	75	nA
		$-40 \le T_A \le +105^{\circ}C$			150	
Ι <sub>Β</sub>	Input Bias Current	T <sub>A</sub> = 25°C		20	150	nA
		$-40 \le T_A \le +105^{\circ}C$			200	
AVD	Large Signal Voltage Gain ( $V_{CC}$ = 15 V, $R_L$ = 2 k $\Omega$ , $V_{OUT}$ = 1.4 V to 11.4 V)	T <sub>A</sub> = 25°C	50	100		V/mV
		$-40 \le T_A \le +105^{\circ}C$	25			
PSRR	Power Supply Rejection (V <sub>CC</sub> = 5 V to 30 V)		80	100		dB

<sup>1.</sup> Guaranteed by design and/or characterization.

#### **ELECTRICAL CHARACTERISTICS (continued)**

Symbol	Characteristics	Conditions	Min	Тур	Max	Unit
OP AMP 2	(INDEPENDENT OP AMP) (continued) (V <sub>CC</sub> = 5.0	V, T <sub>A</sub> = 25°C unless otherwise	noted)	•		•
$V_{\rm ICM}$	Input Common Mode Voltage Range (Note 2) (V <sub>CC</sub> = +30 V)	T <sub>A</sub> = 25°C	0		V <sub>CC</sub> - 1.5	V
		$-40 \le T_A \le +105^{\circ}C$	0		V <sub>CC</sub> - 2.0	
CMRR	Common Mode Rejection Ratio (Note 4)	0 to V <sub>CC</sub> - 1.7 V, T <sub>A</sub> = 25°C	70	85		dB
		$0 \text{ to V}_{CC} - 2.2 \text{ V} \\ -40 \le T_A \le +105^{\circ}\text{C}$	60			
I <sub>SOURCE</sub>	Output Current Source ( $V_{CC}$ = 15 V, $V_{OUT}$ = 2 V, $V_{II}$	<sub>O</sub> = +1 V)	20	40		mA
Ιο	Short-Circuit to GND (V <sub>CC</sub> = 15 V)			40	60	mA
I <sub>SINK</sub>	Output Current Sink (V <sub>ID</sub> = -1 V)	$V_{CC} = +15 \text{ V}, V_{OUT} = 0.2 \text{ V}$	1	10		mA
		V <sub>CC</sub> = +15 V, V <sub>OUT</sub> = 2 V	10	20		mA
V <sub>OH</sub> Output Voltage Swing, Hig	Output Voltage Swing, High (V <sub>CC</sub> = 30 V)	$R_L = 2 \text{ k}\Omega$ , $T_A = 25^{\circ}\text{C}$	26	27		V
		$-40 \le T_A \le +105^{\circ}C$	26			
		R <sub>L</sub> = 10 kΩ, T <sub>A</sub> = 25°C	27	28		
		$-40 \le T_A \le +105^{\circ}C$	27			
V <sub>OL</sub>	Output Voltage Swing, Low	R <sub>L</sub> = 10 kΩ, T <sub>A</sub> = 25°C		5.0	50	mV
SR	Slew Rate (AV = +1, $V_i$ = 0.5 V to 3 V, $V_{CC}$ = 15 V, F	$R_L = 2 \text{ k}\Omega, C_L = 100 \text{ pF}$	0.2	0.4		V/μs
GBP	Gain Bandwidth Product ( $V_{CC}$ = 30 V, AV = +1, R <sub>L</sub> = 2 k $\Omega$ , C <sub>L</sub> = 100 pF, f = 100 kHz, V <sub>IN</sub> = 10 mV <sub>PP</sub> ) (Note 4)		0.5	0.9		MHz
THD	Total Harmonic Distortion (f = 1 kHz, AV = 10, $R_L = 2 k\Omega$ , $V_{CC} = 30 V$ , $V_{OUT} = 2 V_{PP}$ )			0.08		%
e <sub>noise</sub>	Equivalent Input Noise Voltage (f = 1 kHz, R <sub>S</sub> = 100	Ω, V <sub>CC</sub> = 30 V)		50		nV/√ <del>Hz</del>
VOLTAGE	<b>REFERENCE</b> ( $V_{CC}$ = 5.0 V, $T_A$ = 25°C unless otherw	rise noted)				
I <sub>K</sub>	Cathode Current		0.05		100	mA
V <sub>ref</sub>	Reference Voltage (I <sub>K</sub> = 1 mA)	T <sub>A</sub> = 25°C	2.49	2.5	2.51	V
		$-40 \le T_A \le +105^{\circ}C$	2.48	2.5	2.52	
$\Delta V_{ref}$	Reference Deviation over Temperature ( $V_{KA} = V_{ref}$ , +105°C) (Note 4)	$I_{K}$ = 10 mA, $-40 \le T_{A} \le$		7.0	30	mV
I <sub>min</sub>	Minimum Cathode Current for Regulation (2.4875)	/ <sub>f</sub> ≤ V <sub>KA</sub> ≤ 2.5125 V <sub>f</sub> )		10	50	μΑ
I ZKA I	Dynamic Impedance (Note 3) (V <sub>KA</sub> = V <sub>ref</sub> , I <sub>K</sub> = 1 mA to 100 mA, f < 1 kHz)			0.2	0.5	Ω

The input common–mode voltage of either input signal should not be allowed to go negative by more than 0.3 V. The upper end of the common–mode range is V<sub>CC</sub> – 1.5 V. Both inputs can go to V<sub>CC</sub> + 0.3 V without damage.
 The Dynamic Impedance is defined as I ZKA I = ΔV<sub>KA</sub> / ΔI<sub>K</sub>.
 Guaranteed by design and/or characterization.

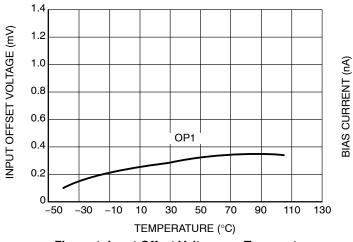


Figure 1. Input Offset Voltage vs. Temperature

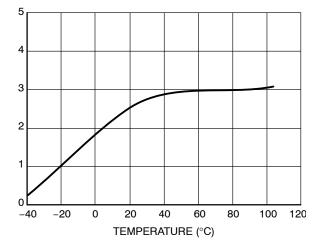


Figure 2. IB vs. Temperature

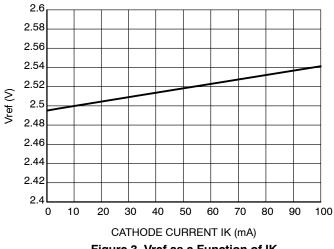


Figure 3. Vref as a Function of IK

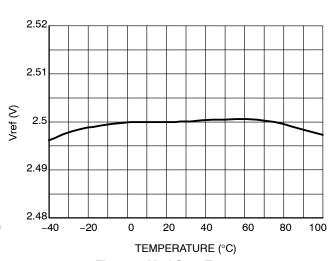


Figure 4. Vref Over Temperature

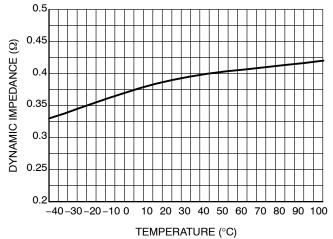
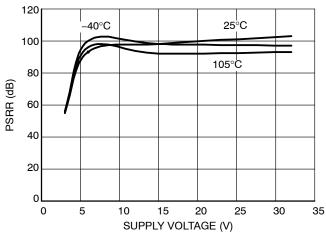


Figure 5. Ref Dynamic Impedance vs. **Temperature** 

120



COMMON MODE REJECTION RATIO (dB) –40°C 100 105<sup>⁰</sup>C 80 25<sup>'</sup>°C 60 40 20 οl 0 35 SUPPLY VOLTAGE (V)

Figure 6. NCS1002A PSRR vs. Supply Voltage

Figure 7. NCS1002A CMRR vs. Supply Voltage

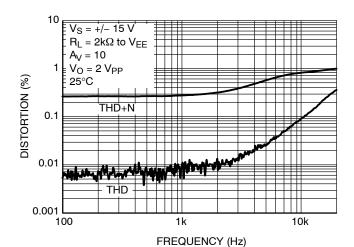


Figure 8. Distortion vs. Frequency

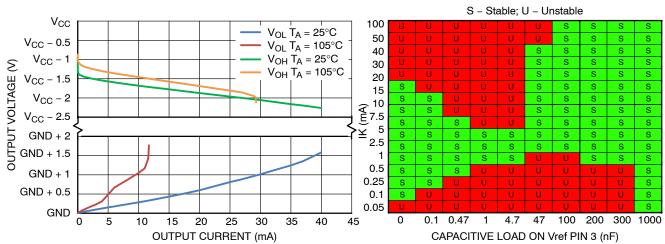


Figure 9. Output Voltage Swing vs. Output Current  $V_{id} = 1 \text{ V}, V_{CM} = 0 \text{ V}, V_{CC} = 3 \text{ V to 36 V}$ 

Figure 10. Region of Reference Stability vs. Capacitive Load (Pin 3)

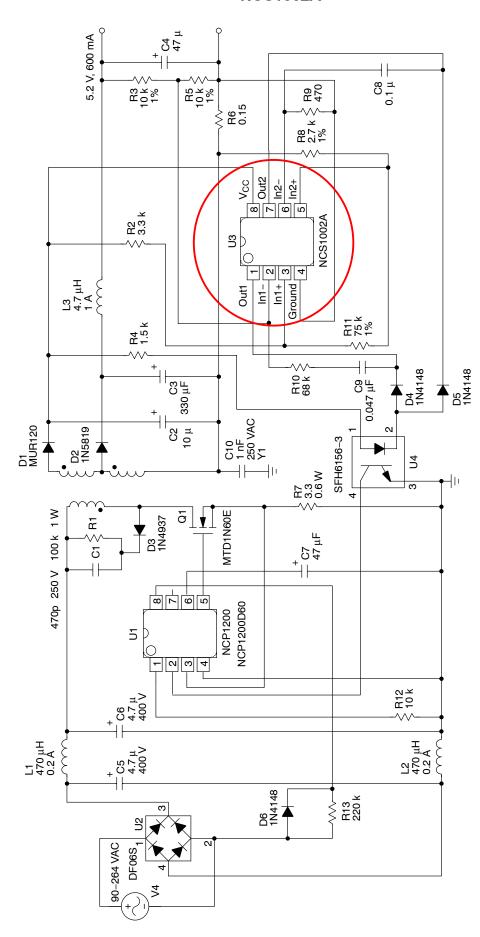


Figure 1. AC Adapter Application

#### **ORDERING INFORMATION**

Device	Package	Shipping <sup>†</sup>
NCS1002ADR2G	SOIC-8 (Pb-Free)	2500 / Tape & Reel

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.





#### SOIC-8 NB CASE 751-07 **ISSUE AK**

**DATE 16 FEB 2011** 



XS

- NOTES:
  1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
  CONTROLLING DIMENSION: MILLIMETER.
- DIMENSION A AND B DO NOT INCLUDE MOLD PROTRUSION.
- MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE
- DIMENSION D DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D DIMENSION AT MAXIMUM MATERIAL CONDITION.
- 751-01 THRU 751-06 ARE OBSOLETE. NEW STANDARD IS 751-07.

	MILLIMETERS		ETERS INCHES		
DIM	MIN	MAX	MIN	MAX	
Α	4.80	5.00	0.189	0.197	
В	3.80	4.00	0.150	0.157	
С	1.35	1.75	0.053	0.069	
D	0.33	0.51	0.013	0.020	
G	1.27	7 BSC	0.050 BSC		
Н	0.10	0.25	0.004	0.010	
J	0.19	0.25	0.007	0.010	
K	0.40	1.27	0.016	0.050	
М	0 °	8 °	0 °	8 °	
N	0.25	0.50	0.010	0.020	
S	5.80	6.20	0.228	0.244	

### **SOLDERING FOOTPRINT\***

0.25 (0.010) M Z Y S



<sup>\*</sup>For additional information on our Pb-Free strategy and soldering details, please download the onsemi Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

#### **GENERIC MARKING DIAGRAM\***



XXXXX = Specific Device Code = Assembly Location = Wafer Lot

= Year = Work Week W = Pb-Free Package

XXXXXX XXXXXX AYWW AYWW H  $\mathbb{H}$ Discrete **Discrete** (Pb-Free)

XXXXXX = Specific Device Code = Assembly Location Α

ww = Work Week

= Pb-Free Package

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

#### **STYLES ON PAGE 2**

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#### SOIC-8 NB CASE 751-07 ISSUE AK

#### **DATE 16 FEB 2011**

STYLE 1: PIN 1. EMITTER 2. COLLECTOR 3. COLLECTOR 4. EMITTER 5. EMITTER 6. BASE 7. BASE 8. EMITTER	STYLE 2: PIN 1. COLLECTOR, DIE, #1 2. COLLECTOR, #1 3. COLLECTOR, #2 4. COLLECTOR, #2 5. BASE, #2 6. EMITTER, #2 7. BASE, #1 8. EMITTER, #1	STYLE 3: PIN 1. DRAIN, DIE #1 2. DRAIN, #1 3. DRAIN, #2 4. DRAIN, #2 5. GATE, #2 6. SOURCE, #2 7. GATE, #1 8. SOURCE, #1	STYLE 4: PIN 1. ANODE 2. ANODE 3. ANODE 4. ANODE 5. ANODE 6. ANODE 7. ANODE 8. COMMON CATHODE
STYLE 5: PIN 1. DRAIN 2. DRAIN 3. DRAIN 4. DRAIN 5. GATE 6. GATE 7. SOURCE 8. SOURCE	STYLE 6: PIN 1. SOURCE 2. DRAIN 3. DRAIN 4. SOURCE 5. SOURCE 6. GATE 7. GATE 8. SOURCE	STYLE 7: PIN 1. INPUT 2. EXTERNAL BYPASS 3. THIRD STAGE SOURCE 4. GROUND 5. DRAIN 6. GATE 3 7. SECOND STAGE Vd 8. FIRST STAGE Vd STYLE 11:	STYLE 8: PIN 1. COLLECTOR, DIE #1 2. BASE, #1 3. BASE, #2
STYLE 9: PIN 1. EMITTER, COMMON 2. COLLECTOR, DIE #1 3. COLLECTOR, DIE #2 4. EMITTER, COMMON 5. EMITTER, COMMON 6. BASE, DIE #2 7. BASE, DIE #1 8. EMITTER, COMMON	STYLE 10: PIN 1. GROUND 2. BIAS 1 3. OUTPUT 4. GROUND 5. GROUND 6. BIAS 2 7. INPUT 8. GROUND	PIN 1. SOURCE 1 2. GATE 1 3. SOURCE 2 4. GATE 2 5. DRAIN 2 6. DRAIN 2 7. DRAIN 1 8. DRAIN 1	PIN 1. SOURCE 2. SOURCE 3. SOURCE 4. GATE 5. DRAIN 6. DRAIN 7. DRAIN 8. DRAIN
STYLE 13: PIN 1. N.C. 2. SOURCE 3. SOURCE 4. GATE 5. DRAIN 6. DRAIN 7. DRAIN 8. DRAIN	STYLE 14: PIN 1. N-SOURCE 2. N-GATE 3. P-SOURCE 4. P-GATE 5. P-DRAIN 6. P-DRAIN 7. N-DRAIN 8. N-DRAIN	STYLE 15: PIN 1. ANODE 1 2. ANODE 1 3. ANODE 1 4. ANODE 1 5. CATHODE, COMMON 6. CATHODE, COMMON 7. CATHODE, COMMON 8. CATHODE, COMMON	STYLE 16:  PIN 1. EMITTER, DIE #1  2. BASE, DIE #1  3. EMITTER, DIE #2  4. BASE, DIE #2  5. COLLECTOR, DIE #2  6. COLLECTOR, DIE #2  7. COLLECTOR, DIE #1  8. COLLECTOR, DIE #1
STYLE 17: PIN 1. VCC 2. V2OUT 3. V10UT 4. TXE 5. RXE 6. VEE 7. GND 8. ACC	STYLE 18: PIN 1. ANODE 2. ANODE 3. SOURCE 4. GATE 5. DRAIN 6. DRAIN 7. CATHODE 8. CATHODE	STYLE 19: PIN 1. SOURCE 1 2. GATE 1 3. SOURCE 2 4. GATE 2 5. DRAIN 2 6. MIRROR 2	STYLE 20: PIN 1. SOURCE (N) 2. GATE (N) 3. SOURCE (P) 4. GATE (P) 5. DRAIN 6. DRAIN
5. RXE 6. VEE 7. GND 8. ACC STYLE 21: PIN 1. CATHODE 1 2. CATHODE 2 3. CATHODE 3 4. CATHODE 4 5. CATHODE 5 6. COMMON ANODE 7. COMMON ANODE 8. CATHODE 6	8. CAHOUE  STYLE 22: PIN 1. I/O LINE 1 2. COMMON CATHODE/VCC 3. COMMON CATHODE/VCC 4. I/O LINE 3 5. COMMON ANODE/GND 6. I/O LINE 4 7. I/O LINE 5 8. COMMON ANODE/GND	7. DHAIN 1 8. MIRROR 1 STYLE 23: PIN 1. LINE 1 IN 2. COMMON ANODE/GND 3. COMMON ANODE/GND 4. LINE 2 IN 5. LINE 2 OUT 6. COMMON ANODE/GND 7. COMMON ANODE/GND 8. LINE 1 OUT	STYLE 24: PIN 1. BASE 2. EMITTER 3. COLLECTOR/ANODE 4. COLLECTOR/ANODE 5. CATHODE 6. CATHODE 7. COLLECTOR/ANODE 8. COLLECTOR/ANODE
STYLE 25: PIN 1. VIN 2. N/C 3. REXT 4. GND 5. IOUT 6. IOUT 7. IOUT 8. IOUT	STYLE 26: PIN 1. GND 2. dv/dt 3. ENABLE 4. ILIMIT 5. SOURCE 6. SOURCE 7. SOURCE 8. VCC	STYLE 27: PIN 1. ILIMIT 2. OVLO 3. UVLO 4. INPUT+ 5. SOURCE 6. SOURCE 7. SOURCE 8. DRAIN	STYLE 28: PIN 1. SW_TO_GND 2. DASIC_OFF 3. DASIC_SW_DET 4. GND 5. V_MON 6. VBULK 7. VBULK 8. VIN
STYLE 29: PIN 1. BASE, DIE #1 2. EMITTER, #1 3. BASE, #2 4. EMITTER, #2 5. COLLECTOR, #2 6. COLLECTOR, #2 7. COLLECTOR, #1 8. COLLECTOR, #1	STYLE 30: PIN 1. DRAIN 1 2. DRAIN 1 3. GATE 2 4. SOURCE 2 5. SOURCE 1/DRAIN 2 6. SOURCE 1/DRAIN 2 7. SOURCE 1/DRAIN 2 8. GATE 1		

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